

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ max	I_D max $T_A = +25^\circ\text{C}$
30V	12m Ω @ $V_{GS} = 10\text{V}$	10A
	16m Ω @ $V_{GS} = 4.5\text{V}$	8.5A

Features and Benefits

- 0.6mm profile – ideal for low profile applications
- PCB footprint of 4mm²
- Low Gate Threshold Voltage
- Low On-Resistance
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Description and Applications

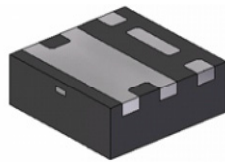
This MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Battery Management Application
- Power Management Functions
- DC-DC Converters

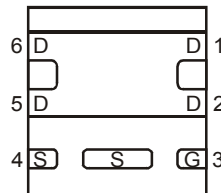
Mechanical Data

- Case: U-DFN2020-6 Type E
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.0065 grams (approximate)

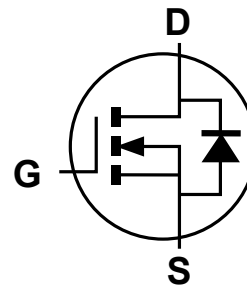
U-DFN2020-6
Type E



Bottom View



Pin Out



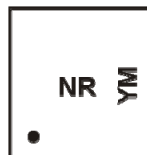
Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3016LFDE-7	U-DFN2020-6 Type E	3,000/Tape & Reel
DMN3016LFDE-13	U-DFN2020-6 Type E	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



NR = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: Y = 2011)
 M = Month (ex: 9 = September)

Date Code Key

Year	2011	2012	2013	2014	2015	2016	2017
Code	Y	Z	A	B	C	D	E

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current (Note 6) $V_{GS} = 10\text{V}$	Steady State	$T_A = +25^\circ\text{C}$	10
		$T_A = +70^\circ\text{C}$	8
	$t < 10\text{s}$	$T_A = +25^\circ\text{C}$	12
		$T_A = +70^\circ\text{C}$	9
Maximum Continuous Body Diode Forward Current (Note 6)	I_S	2.5	A
Pulsed Drain Current (10 μs pulse, duty cycle = 1%)	I_{DM}	90	A
Avalanche Current (Note 7) $L = 0.1\text{mH}$	I_{AR}	22	A
Repetitive Avalanche Energy (Note 7) $L = 0.1\text{mH}$	E_{AR}	24	mJ

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P_D	$T_A = +25^\circ\text{C}$	0.73
		$T_A = +70^\circ\text{C}$	0.47
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	Steady state	171
		$t < 10\text{s}$	121
Total Power Dissipation (Note 6)	P_D	$T_A = +25^\circ\text{C}$	2.02
		$T_A = +70^\circ\text{C}$	1.30
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	Steady state	62
		$t < 10\text{s}$	42
Thermal Resistance, Junction to Case (Note 6)	$R_{\theta JC}$	9.3	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	-	-	V	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current	I_{DSS}	-	-	1	μA	$V_{DS} = 30\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	-	-	± 100	nA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(th)}$	1.4	-	2.0	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(on)}$	-	8	12	m Ω	$V_{GS} = 10\text{V}, I_D = 11\text{A}$
		-	12	16		$V_{GS} = 4.5\text{V}, I_D = 9\text{A}$
Forward Transfer Admittance	$ Y_{fs} $	-	32	-	S	$V_{DS} = 5\text{V}, I_D = 12\text{A}$
Diode Forward Voltage	V_{SD}	-	0.70	1.0	V	$V_{GS} = 0\text{V}, I_S = 1\text{A}$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	-	1415	-	pF	$V_{DS} = 15\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	-	119	-		
Reverse Transfer Capacitance	C_{rss}	-	82	-		
Gate resistance	R_g	-	2.6	3.2	Ω	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Total Gate Charge ($V_{GS} = 4.5\text{V}$)	Q_g	-	11.3	-	nC	$V_{DS} = 15\text{V}, I_D = 12\text{A}$
Total Gate Charge ($V_{GS} = 10\text{V}$)	Q_g	-	25.1	-		
Gate-Source Charge	Q_{gs}	-	3.5	-		
Gate-Drain Charge	Q_{gd}	-	3.6	-		
Turn-On Delay Time	$t_{D(on)}$	-	4.8	-	ns	$V_{DD} = 15\text{V}, V_{GS} = 10\text{V}, R_L = 1.25\Omega, R_G = 3\Omega,$
Turn-On Rise Time	t_r	-	16.5	-		
Turn-Off Delay Time	$t_{D(off)}$	-	26.1	-		
Turn-Off Fall Time	t_f	-	5.6	-		
Reverse Recovery Time	t_{rr}	-	12.3	-	ns	$I_F = 12\text{A}, di/dt = 500\text{A}/\mu\text{s}$
Reverse Recovery Charge	Q_{rr}	-	10.4	-	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - I_{AR} and E_{AR} rating are based on low frequency and duty cycles to keep $T_J = +25^\circ\text{C}$
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

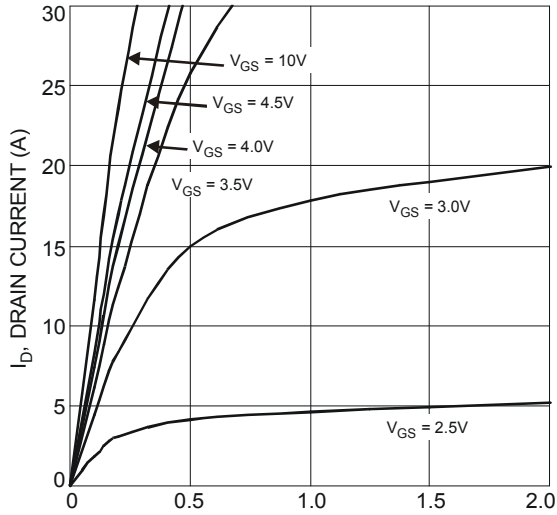


Fig. 1 Typical Output Characteristics

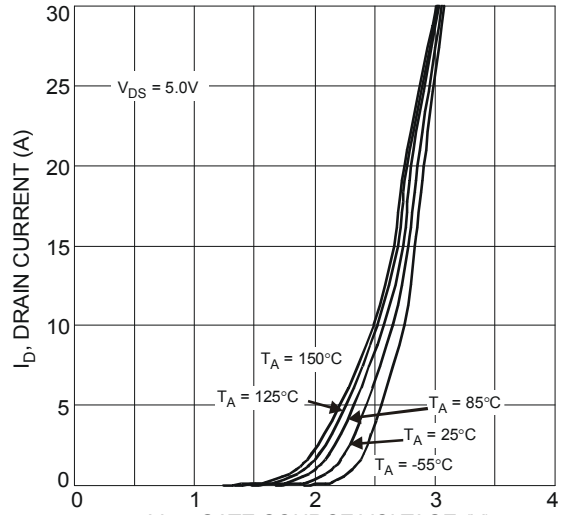


Fig. 2 Typical Transfer Characteristics

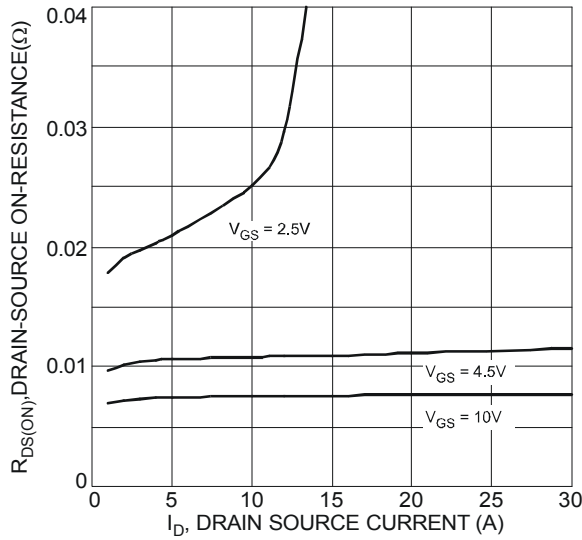


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

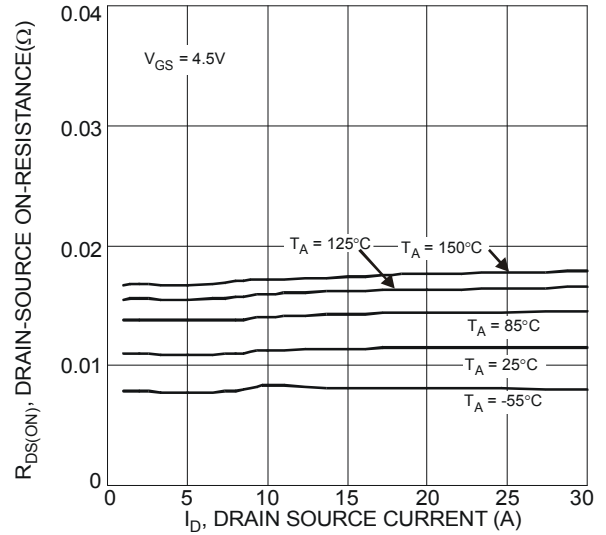


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

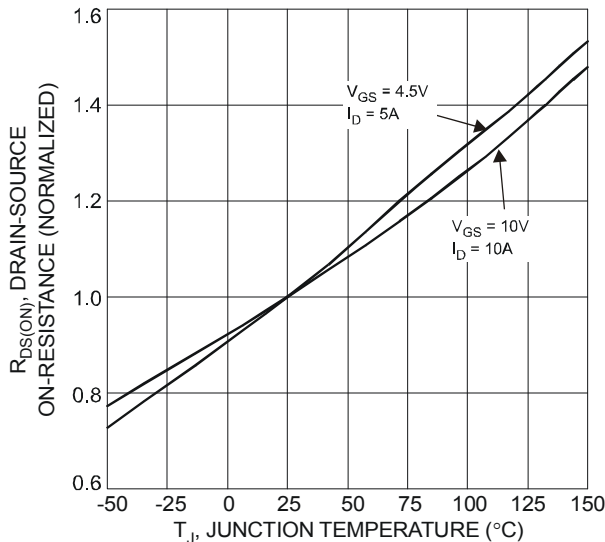


Fig. 5 On-Resistance Variation with Temperature

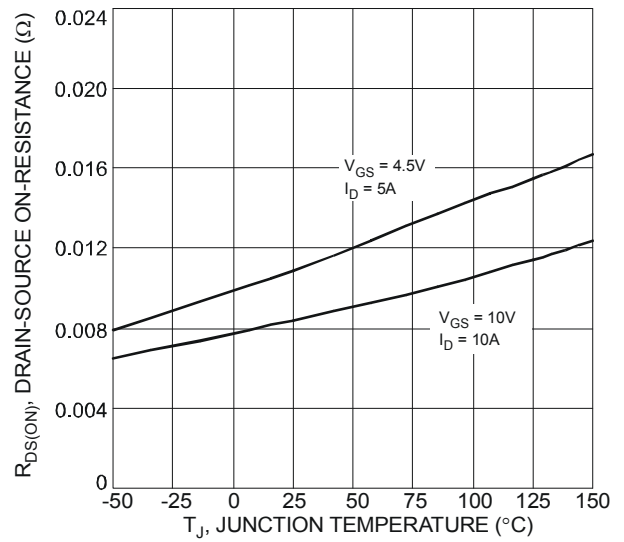


Fig. 6 On-Resistance Variation with Temperature

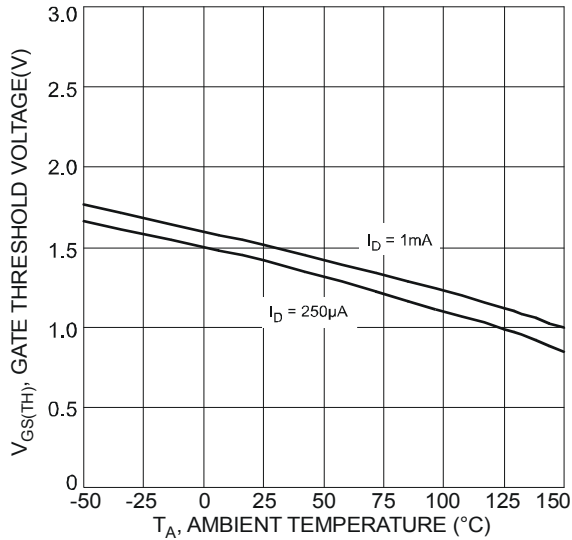


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

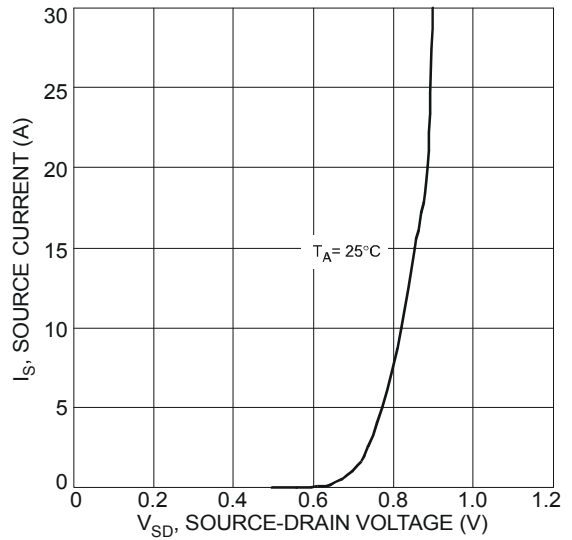


Fig. 8 Diode Forward Voltage vs. Current

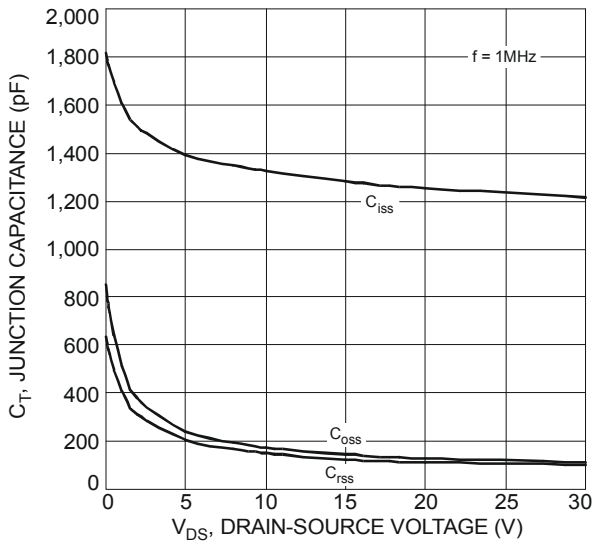


Fig. 9 Typical Junction Capacitance

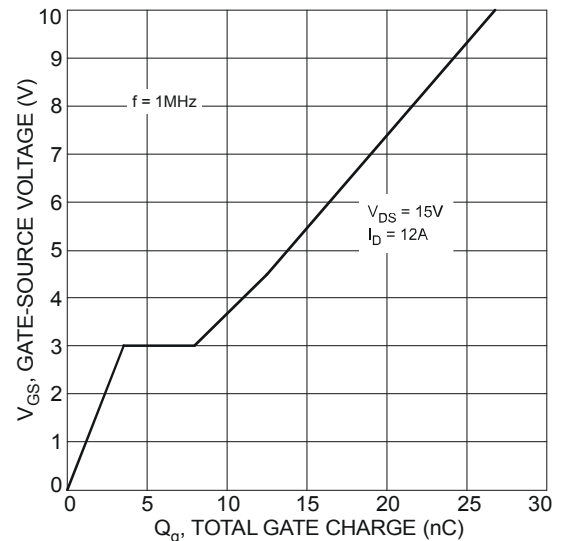


Fig. 10 Gate-Charge Characteristics

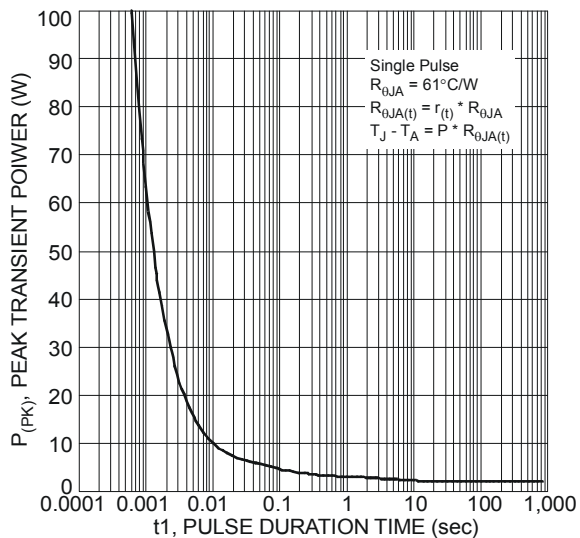
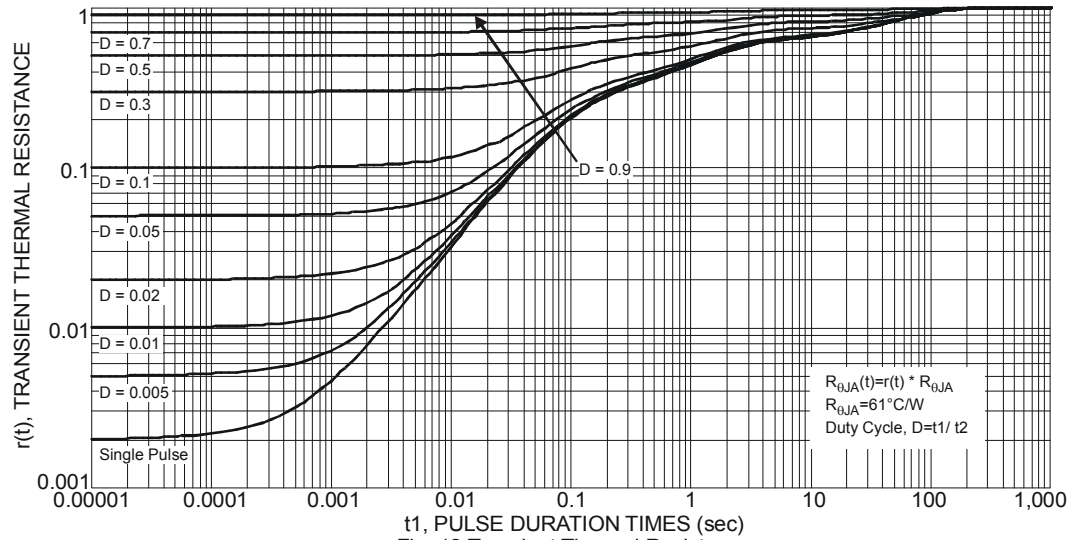
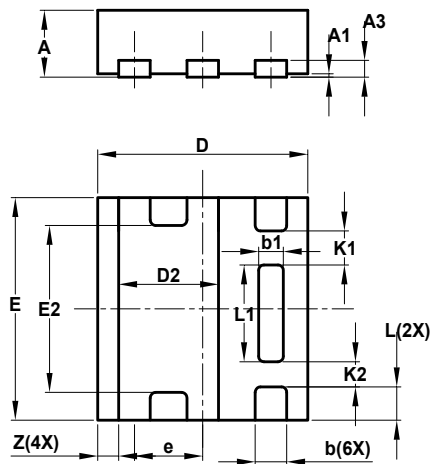


Fig. 11 Single Pulse Maximum Power Dissipation



Package Outline Dimension

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.

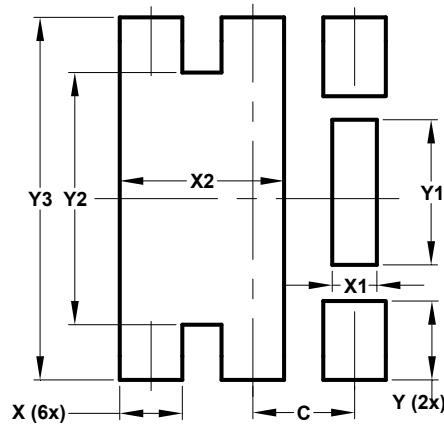


U-DFN2020-6 Type E			
Dim	Min	Max	Typ
A	0.57	0.63	0.60
A1	0	0.05	0.03
A3	-	-	0.15
b	0.25	0.35	0.30
b1	0.185	0.285	0.235
D	1.95	2.05	2.00
D2	0.85	1.05	0.95
E	1.95	2.05	2.00
E2	1.40	1.60	1.50
e	-	-	0.65
L	0.25	0.35	0.30
L1	0.82	0.92	0.87
K1	-	-	0.305
K2	-	-	0.225
Z	-	-	0.20

All Dimensions in mm

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	0.650
X	0.400
X1	0.285
X2	1.050
Y	0.500
Y1	0.920
Y2	1.600
Y3	2.300

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